

Abstract of the Disclosure:

A compensation component, in which a lateral section and, at least at one end of the lateral section, a section that is inclined with respect to the surface of a drift path, includes
5 n-conducting and p-conducting regions completely embedded in a semiconductor body without a trench. In such a case, the inclined section is formed by ion implantation through an implantation mask with an inclined edge.

GLM/nt